AD617684

TRANSLATION

METHOD OF CREATING p-n TRANSFERS

Ву

I. I. Patalakh, I. M. Kustanovich, and L. S. Polak

S. 1.00

S. 1.00

S. 1.00

S-1.

FOREIGN TECHNOLOGY DIVISION

AIR FORCE SYSTEMS COMMAND

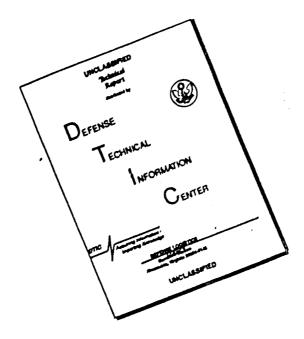
WRIGHT PATTERSON AIR FORCE BASE

Jane

JUL 19 1965

LINGTHIVE COPY

DISCLAIMER NOTICE



THIS DOCUMENT IS BEST QUALITY AVAILABLE. THE COPY FURNISHED TO DTIC CONTAINED A SIGNIFICANT NUMBER OF PAGES WHICH DO NOT REPRODUCE LEGIBLY.

		h the basic es	
			al terminology.

UNEDITED ROUGH DRAFT TRANSLATION

METHOD OF CREATING p-n TRANSFERS

BY: I. I. Patalakh, I. M. Kustanovich, and L. S. Polak

English pages: 2

SOURCE: Patent No. 161074 (Appl. No. 798839 26-9,

October 15, 1962), (Russian), l page.

TA5001057

THIS TRANSLATION IS A RENDITION OF THE ORIGINAL FOREIGN TEXT WITHOUT ANY ANALYTICAL OR EDITORIAL COMMENT. STATEMENTS OR THEORIES ADVOCATED OR IMPLIED ARE THOSE OF THE SOURCE AND DO NOT NECESSARILY REFLECT THE POSITION OR OPINION OF THE FOREIGN TECHNOLOGY DIVISION.

PREPARED BY

TRANSLATION DIVISION
FOREIGN TECHNOLOGY DIVISION
WP-AFB, ONIO.

FTD-TT- 65-237, 1+4

Date . July 19 .

METHOD OF CREATING p-n TRANSFERS

by

I. I. Patalakh, I. M. Kustamovich and L. S. Polak

Nethods are known for creating organic semiconductor materials with a definite type of conductivity through the introduction into them of atoms of metal as an admixture.

There is proposed a method of creating p-n transfers on organic and inorganic polymer semiconductor materials based on the use of different signs of the carrying current in the surface layer and volume of these polymers.

The method is accomplished in the following fashion.

The surface of the polymer semiconductor specimen is freed from adsorption substances (for example, by heating in vacuum). On the surface free of adsorption there is applied an electrode in such a way that the surface of the semiconductor material with the electrode be dependably protected against adsorption, after which on the unprotected areas of the specimen substance is adsorbed (for example, oxygen, iodine and bromine) which has a reverse volumetric type of conductivity, as a result of which there is formed a p—n transition of this area. On the area with the opposite type of conductivity there is created an obmic contact.

The proposed method of obtaining a p-n transition in polymetric semiconductor materials makes it possible to use these materials as radio-technology details, the working of which is based on the properties of the p-n transition.

Object of the Invention

Method of creating p-n transfers on organic and inorganic polymeric semiconductor materials base on the use of different signs of the carrier current in the surface layer and volume of these polymers which has the distinguishing feature that for the purpose of using the indicated materials for preparing the semiconductor instruments, the surface of the polymeric semiconductor specimen is cleaned of the adsorbent layer of admixtures by one of known methods (for example, heating in a vacuum). On the area of the cleaned surface there is created an ohmic contact, the electrode of which protects the surface of contact from the adsorption of admixtures. On the unprotected areas of the specimen substance is adsorbed which has the opposite volumetric type of conductivity, after which on the area with the opposite type of conductivity there was created an ohmic contact.

CLEARINGHOUSE FOR FEDERAL SCIENTIFIC AND TECHNICAL INFORMATION, CESTI INPUT SECTION 410.11

AD 617684

LIMITATIONS IN REPRODUCTION QUALITY OF TECHNICAL ABSTRACT BULLETIN DOCUMENTS, DEFENSE DOCUMENTATION CENTER (DDC)

	1.		AVAILABLE ONLY FOR REFERENCE USE AT DDC FIELD SERVICES. COPY IS NOT AVAILABLE FOR PUBLIC SALE.
Х	2.		AVAILABLE COPY WILL NOT PERMIT FULLY LEGIBLE REPRODUCTION. REPRODUCTION WILL BE MADE IF REQUESTED BY USERS OF DDC.
X		Α.	COPY IS AVAILABLE FOR PUBLIC SALE.
		В.	COPY IS NOT AVAILABLE FOR PUBLIC SALE.
	3.		LIMITED NUMBER OF COPIES CONTAINING COLOR OTHER THAN BLACK AND WHITE ARE AVAILABLE UNTIL STOCK IS EXHAUSTED. REPRODUCTIONS WILL BE MADE IN BLACK AND WHITE ONLY

TSL-121-2 65

DATE PROCESSED: 7/21/65
PROCESSOR: (Suitter